Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	93
Number of Gates	250000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/m1afs250-1pqg208i

2 – Device Architecture

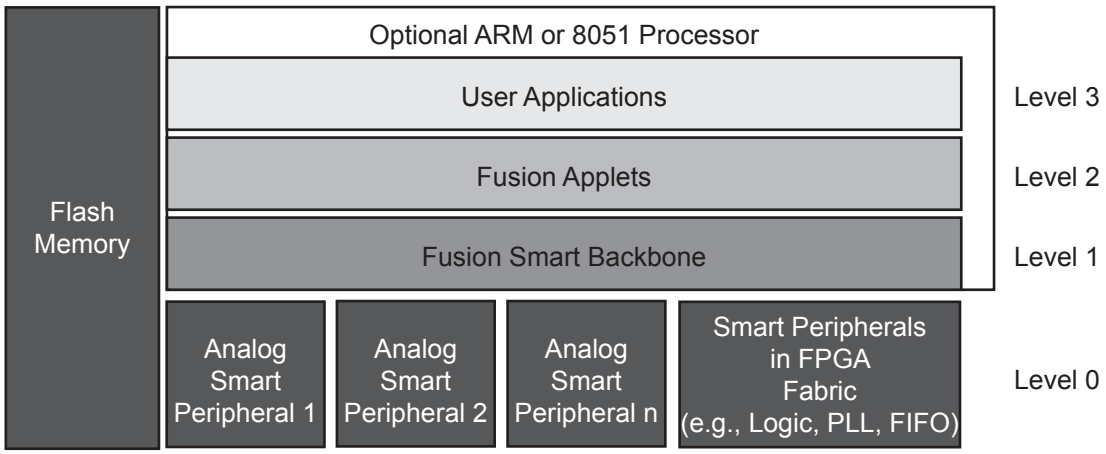
Fusion Stack Architecture

To manage the unprecedented level of integration in Fusion devices, Microsemi developed the Fusion technology stack (Figure 2-1). This layered model offers a flexible design environment, enabling design at very high and very low levels of abstraction. Fusion peripherals include hard analog IP and hard and soft digital IP. Peripherals communicate across the FPGA fabric via a layer of soft gates—the Fusion backbone. Much more than a common bus interface, this Fusion backbone integrates a micro-sequencer within the FPGA fabric and configures the individual peripherals and supports low-level processing of peripheral data. Fusion applets are application building blocks that can control and respond to peripherals and other system signals. Applets can be rapidly combined to create large applications. The technology is scalable across devices, families, design types, and user expertise, and supports a well-defined interface for external IP and tool integration.

At the lowest level, Level 0, are Fusion peripherals. These are configurable functional blocks that can be hardwired structures such as a PLL or analog input channel, or soft (FPGA gate) blocks such as a UART or two-wire serial interface. The Fusion peripherals are configurable and support a standard interface to facilitate communication and implementation.

Connecting and controlling access to the peripherals is the Fusion backbone, Level 1. The backbone is a soft-gate structure, scalable to any number of peripherals. The backbone is a bus and much more; it manages peripheral configuration to ensure proper operation. Leveraging the common peripheral interface and a low-level state machine, the backbone efficiently offloads peripheral management from the system design. The backbone can set and clear flags based upon peripheral behavior and can define performance criteria. The flexibility of the stack enables a designer to configure the silicon, directly bypassing the backbone if that level of control is desired.

One step up from the backbone is the Fusion applet, Level 2. The applet is an application building block that implements a specific function in FPGA gates. It can react to stimuli and board-level events coming through the backbone or from other sources, and responds to these stimuli by accessing and manipulating peripherals via the backbone or initiating some other action. An applet controls or responds to the peripheral(s). Applets can be easily imported or exported from the design environment. The applet structure is open and well-defined, enabling users to import applets from Microsemi, system developers, third parties, and user groups.



Note: Levels 1, 2, and 3 are implemented in FPGA logic gates.

Figure 2-1 • **Fusion Architecture Stack**

Table 2-7 • AFS250 Global Resource Timing
Commercial Temperature Range Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2		–1		Std.		Units
		Min.[1]	Max.[2]	Min.[1]	Max.[2]	Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	0.89	1.12	1.02	1.27	1.20	1.50	ns
t_{RCKH}	Input High Delay for Global Clock	0.88	1.14	1.00	1.30	1.17	1.53	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock							ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock							ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.30		0.35	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For the derating values at specific junction temperature and voltage supply levels, refer to Table 3-7 on page 3-9.*

Table 2-8 • AFS090 Global Resource Timing
Commercial Temperature Range Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	–2		–1		Std.		Units
		Min.[1]	Max.[2]	Min.[1]	Max.[2]	Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	0.84	1.07	0.96	1.21	1.13	1.43	ns
t_{RCKH}	Input High Delay for Global Clock	0.83	1.10	0.95	1.25	1.12	1.47	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock							ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock							ns
t_{RCKSW}	Maximum Skew for Global Clock		0.27		0.30		0.36	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For the derating values at specific junction temperature and voltage supply levels, refer to Table 3-7 on page 3-9.*

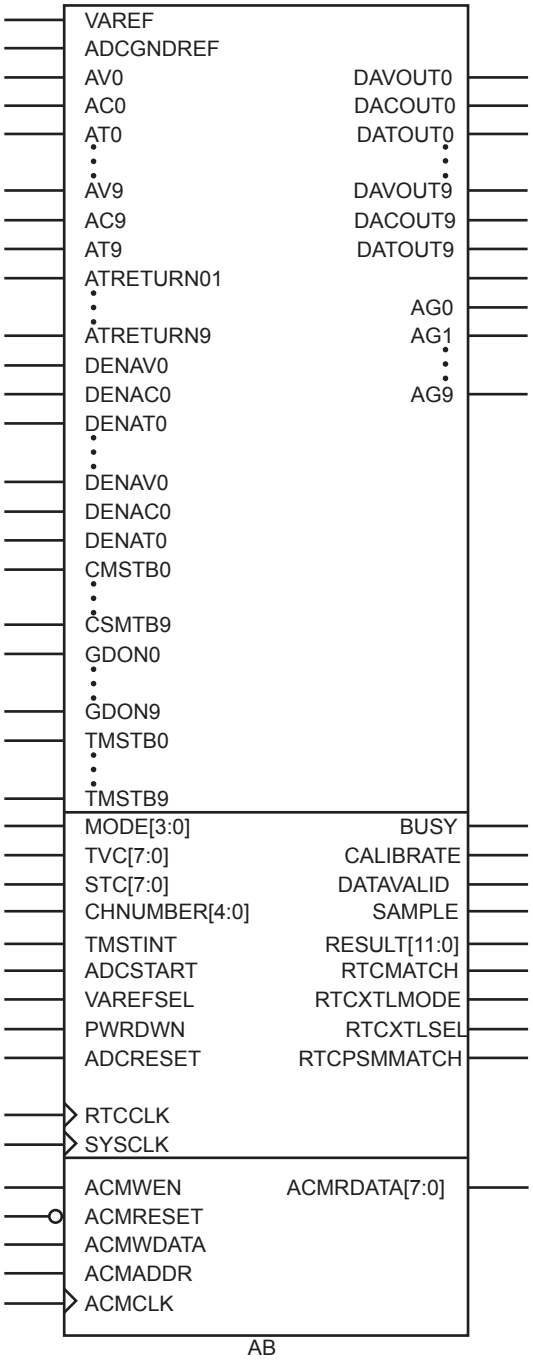


Figure 2-64 • **Analog Block Macro**

Fusion uses a remote diode as a temperature sensor. The Fusion Temperature Monitor uses a differential input; the AT pin and ATRTN (AT Return) pin are the differential inputs to the Temperature Monitor. There is one Temperature Monitor in each Quad. A simplified block diagram is shown in Figure 2-77.

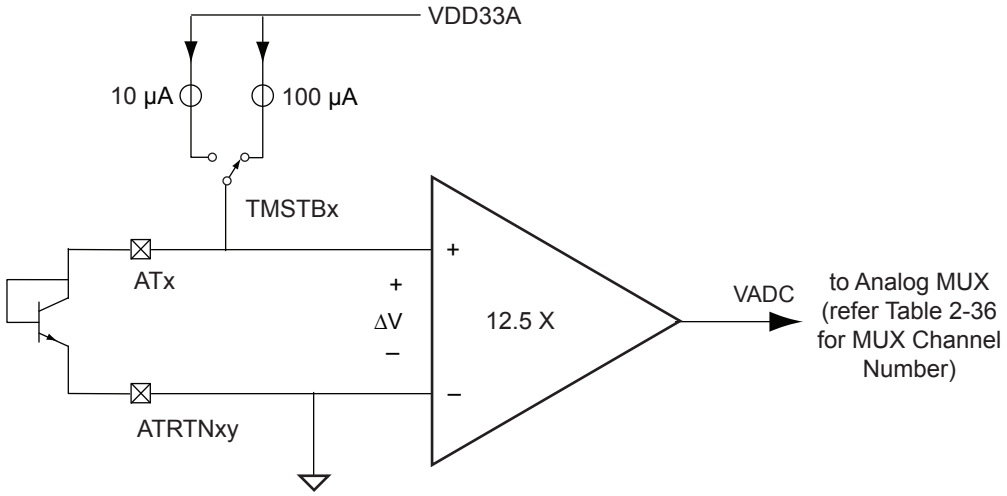


Figure 2-77 • **Block Diagram for Temperature Monitor Circuit**

The Fusion approach to measuring temperature is forcing two different currents through the diode with a ratio of 10:1. The switch that controls the different currents is controlled by the Temperature Monitor Strobe signal, TMSTB. Setting TMSTB to '1' will initiate a Temperature reading. The TMSTB should remain '1' until the ADC finishes sampling the voltage from the Temperature Monitor. The minimum sample time for the Temperature Monitor cannot be less than the minimum strobe high time minus the setup time. Figure 2-78 shows the timing diagram.

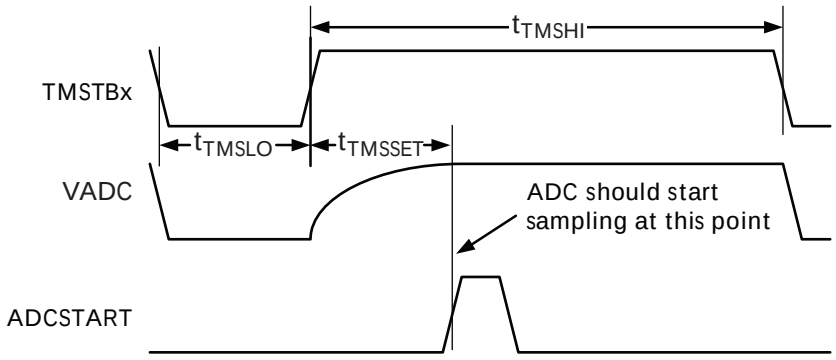


Figure 2-78 • **Timing Diagram for the Temperature Monitor Strobe Signal**

Note: When the IEEE 1149.1 Boundary Scan EXTEST instruction is executed, the AG pad drive strength ceases and becomes a 1 µA sink into the Fusion device.

Integrated Voltage Reference

The Fusion device has an integrated on-chip 2.56 V reference voltage for the ADC. The value of this reference voltage was chosen to make the prescaling and postscaling factors for the prescaler blocks change in a binary fashion. However, if desired, an external reference voltage of up to 3.3 V can be connected between the VAREF and ADCGNDREF pins. The VAREFSEL control pin is used to select the reference voltage.

Table 2-42 • VAREF Bit Function

Name	Bit	Function
VAREF	0	Reference voltage selection 0 – Internal voltage reference selected. VAREF pin outputs 2.56 V. 1 – Input external voltage reference from VAREF and ADCGNDREF

ADC Clock

The speed of the ADC depends on its internal clock, ADCCLK, which is not accessible to users. The ADCCLK is derived from SYSCLK. Input signal TVC[7:0], Time Divider Control, determines the speed of the ADCCLK in relationship to SYSCLK, based on EQ 15.

$$t_{ADCCLK} = 4 \times (1 + TVC) \times t_{SYSCLK}$$

EQ 15

TVC: Time Divider Control (0–255)

t_{ADCCLK} is the period of ADCCLK, and must be between 0.5 MHz and 10 MHz

t_{SYSCLK} is the period of SYSCLK

Table 2-43 • TVC Bits Function

Name	Bits	Function
TVC	[7:0]	SYSCLK divider control

The frequency of ADCCLK, f_{ADCCLK}, must be within 0.5 Hz to 10 MHz.

The inputs to the ADC are synchronized to SYSCLK. A conversion is initiated by asserting the ADCSTART signal on a rising edge of SYSCLK. Figure 2-90 on page 2-112 and Figure 2-91 on page 2-112 show the timing diagram for the ADC.

Acquisition Time or Sample Time Control

Acquisition time (t_{SAMPLE}) specifies how long an analog input signal has to charge the internal capacitor array. Figure 2-88 shows a simplified internal input sampling mechanism of a SAR ADC.

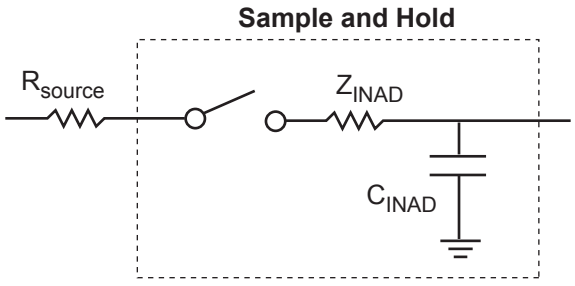


Figure 2-88 • Simplified Sample and Hold Circuitry

The internal impedance (Z_{INAD}), external source resistance (R_{SOURCE}), and sample capacitor (C_{INAD}) form a simple RC network. As a result, the accuracy of the ADC can be affected if the ADC is given insufficient time to charge the capacitor. To resolve this problem, you can either reduce the source resistance or increase the sampling time by changing the acquisition time using the STC signal.

Table 2-57 details the settings available to control the prescaler values of the AV, AC, and AT pins. Note that the AT pin has a reduced number of available prescaler values.

***Table 2-57* • Prescaler Control Truth Table—AV (x = 0), AC (x = 1), and AT (x = 3)**

Control Lines Bx[2:0]	Scaling Factor, Pad to ADC Input	LSB for an 8-Bit Conversion[1] (mV)	LSB for a 10-Bit Conversion[1] (mV)	LSB for a 12-Bit Conversion[1] (mV)	Full-Scale Voltage in 10-Bit Mode[2]	Range Name
000 [3]	0.15625	64	16	4	16.368 V	16 V
001	0.3125	32	8	2	8.184 V	8 V
010 [3]	0.625	16	4	1	4.092 V	4 V
011	1.25	8	2	0.5	2.046 V	2 V
100	2.5	4	1	0.25	1.023 V	1 V
101	5.0	2	0.5	0.125	0.5115 V	0.5 V
110	10.0	1	0.25	0.0625	0.25575 V	0.25 V
111	20.0	0.5	0.125	0.03125	0.127875 V	0.125 V

Notes:

1. *LSB voltage equivalences assume VAREF = 2.56 V.*
2. *Full Scale voltage for n-bit mode: ((2^n) - 1) x (LSB for a n-bit Conversion)*
3. *These are the only valid ranges for the Temperature Monitor Block Prescaler.*

Table 2-58 details the settings available to control the MUX within each of the AV, AC, and AT circuits. This MUX determines whether the signal routed to the ADC is the direct analog input, prescaled signal, or output of either the Current Monitor Block or the Temperature Monitor Block.

***Table 2-58* • Analog Multiplexer Truth Table—AV (x = 0), AC (x = 1), and AT (x = 3)**

Control Lines Bx[4]	Control Lines Bx[3]	ADC Connected To
0	0	Prescaler
0	1	Direct input
1	0	Current amplifier temperature monitor
1	1	Not valid

Table 2-59 details the settings available to control the Direct Analog Input switch for the AV, AC, and AT pins.

***Table 2-59* • Direct Analog Input Switch Control Truth Table—AV (x = 0), AC (x = 1), and AT (x = 3)**

Control Lines Bx[5]	Direct Input Switch
0	Off
1	On

Table 2-60 details the settings available to control the polarity of the signals coming to the AV, AC, and AT pins. Note that the only valid setting for the AT pin is logic 0 to support positive voltages.

Table 2-60* • Voltage Polarity Control Truth Table—AV (x = 0), AC (x = 1), and AT (x = 3)

Control Lines Bx[6]	Input Signal Polarity
0	Positive
1	Negative

*Note: *The B3[6] signal for the AT pad should be kept at logic 0 to accept only positive voltages.*

***Table 2-68* • I/O Bank Support by Device**

I/O Bank	AFS090	AFS250	AFS600	AFS1500
Standard I/O	N	N	–	–
Advanced I/O	E, W	E, W	E, W	E, W
Pro I/O	–	–	N	N
Analog Quad	S	S	S	S

Note: E = East side of the device
W = West side of the device
N = North side of the device
S = South side of the device

***Table 2-69* • Fusion VCCI Voltages and Compatible Standards**

VCCI (typical)	Compatible Standards
3.3 V	LVTTL/LVCMOS 3.3, PCI 3.3, SSTL3 (Class I and II),* GTL+ 3.3, GTL 3.3,* LVPECL
2.5 V	LVCMOS 2.5, LVCMOS 2.5/5.0, SSTL2 (Class I and II),* GTL+ 2.5,* GTL 2.5,* LVDS, BLVDS, M-LVDS
1.8 V	LVCMOS 1.8
1.5 V	LVCMOS 1.5, HSTL (Class I),* HSTL (Class II)*

*Note: *I/O standard supported by Pro I/O banks.*

Table 2-70* • Fusion VREF Voltages and Compatible Standards

VREF (typical)	Compatible Standards
1.5 V	SSTL3 (Class I and II)
1.25 V	SSTL2 (Class I and II)
1.0 V	GTL+ 2.5, GTL+ 3.3
0.8 V	GTL 2.5, GTL 3.3
0.75 V	HSTL (Class I), HSTL (Class II)

*Note: *I/O standards supported by Pro I/O banks.*

Electrostatic Discharge (ESD) Protection

Fusion devices are tested per JEDEC Standard JESD22-A114-B.

Fusion devices contain clamp diodes at every I/O, global, and power pad. Clamp diodes protect all device pads against damage from ESD as well as from excessive voltage transients.

Each I/O has two clamp diodes. One diode has its positive (P) side connected to the pad and its negative (N) side connected to VCCI. The second diode has its P side connected to GND and its N side connected to the pad. During operation, these diodes are normally biased in the Off state, except when transient voltage is significantly above VCCI or below GND levels.

By selecting the appropriate I/O configuration, the diode is turned on or off. Refer to Table 2-75 and Table 2-76 on page 2-143 for more information about I/O standards and the clamp diode.

The second diode is always connected to the pad, regardless of the I/O configuration selected.

***Table 2-75* • Fusion Standard and Advanced I/O – Hot-Swap and 5 V Input Tolerance Capabilities**

I/O Assignment	Clamp Diode		Hot Insertion		5 V Input Tolerance [1]		Input Buffer	Output Buffer
	Standard I/O	Advanced I/O	Standard I/O	Advanced I/O	Standard I/O	Advanced I/O		
3.3 V LVTTL/LVCMOS	No	Yes	Yes	No	Yes[1]	Yes[1]	Enabled/Disabled	
3.3 V PCI, 3.3 V PCI-X	N/A	Yes	N/A	No	N/A	Yes[1]	Enabled/Disabled	
LVCMOS 2.5 V	No	Yes	Yes	No	No	No	Enabled/Disabled	
LVCMOS 2.5 V / 5.0 V	N/A	Yes	N/A	No	N/A	Yes[2]	Enabled/Disabled	
LVCMOS 1.8 V	No	Yes	Yes	No	No	No	Enabled/Disabled	
LVCMOS 1.5 V	No	Yes	Yes	No	No	No	Enabled/Disabled	
Differential, LVDS/BLVDS/M-LVDS/ LVPECL [3]	N/A	Yes	N/A	No	N/A	No	Enabled/Disabled	

Notes:

1. *Can be implemented with an external IDT bus switch, resistor divider, or Zener with resistor.*
2. *Can be implemented with an external resistor and an internal clamp diode.*
3. *Bidirectional LVPECL buffers are not supported. I/Os can be configured as either input buffers or output buffers.*

***Table 2-76* • Fusion Pro I/O – Hot-Swap and 5 V Input Tolerance Capabilities**

I/O Assignment	Clamp Diode	Hot Insertion	5 V Input Tolerance	Input Buffer	Output Buffer
3.3 V LVTTL/LVCMOS	No	Yes	Yes[1]	Enabled/Disabled	
3.3 V PCI, 3.3 V PCI-X	Yes	No	Yes[1]	Enabled/Disabled	
LVCMOS 2.5 V [3]	No	Yes	No	Enabled/Disabled	
LVCMOS 2.5 V / 5.0 V [3]	Yes	No	Yes[2]	Enabled/Disabled	
LVCMOS 1.8 V	No	Yes	No	Enabled/Disabled	
LVCMOS 1.5 V	No	Yes	No	Enabled/Disabled	
Voltage-Referenced Input Buffer	No	Yes	No	Enabled/Disabled	
Differential, LVDS/BLVDS/M-LVDS/LVPECL[4]	No	Yes	No	Enabled/Disabled	

Notes:

1. *Can be implemented with an external IDT bus switch, resistor divider, or Zener with resistor.*
2. *Can be implemented with an external resistor and an internal clamp diode.*
3. *In the SmartGen, FlashROM, Flash Memory System Builder, and Analog System Builder User Guide, select the LVCMOS5 macro for the LVCMOS 2.5 V / 5.0 V I/O standard or the LVCMOS25 macro for the LVCMOS 2.5 V I/O standard.*
4. *Bidirectional LVPECL buffers are not supported. I/Os can be configured as either input buffers or output buffers.*

5 V Output Tolerance

Fusion I/Os must be set to 3.3 V LVTTL or 3.3 V LVCMOS mode to reliably drive 5 V TTL receivers. It is also critical that there be NO external I/O pull-up resistor to 5 V, since this resistor would pull the I/O pad voltage beyond the 3.6 V absolute maximum value and consequently cause damage to the I/O.

When set to 3.3 V LVTTL or 3.3 V LVCMOS mode, Fusion I/Os can directly drive signals into 5 V TTL receivers. In fact, VOL = 0.4 V and VOH = 2.4 V in both 3.3 V LVTTL and 3.3 V LVCMOS modes exceed the VIL = 0.8 V and VIH = 2 V level requirements of 5 V TTL receivers. Therefore, level '1' and level '0' will be recognized correctly by 5 V TTL receivers.

Simultaneously Switching Outputs and PCB Layout

- Simultaneously switching outputs (SSOs) can produce signal integrity problems on adjacent signals that are not part of the SSO bus. Both inductive and capacitive coupling parasitics of bond wires inside packages and of traces on PCBs will transfer noise from SSO busses onto signals adjacent to those busses. Additionally, SSOs can produce ground bounce noise and VCCI dip noise. These two noise types are caused by rapidly changing currents through GND and VCCI package pin inductances during switching activities:
- Ground bounce noise voltage = L(GND) * di/dt
- VCCI dip noise voltage = L(VCCI) * di/dt

Any group of four or more input pins switching on the same clock edge is considered an SSO bus. The shielding should be done both on the board and inside the package unless otherwise described.

In-package shielding can be achieved in several ways; the required shielding will vary depending on whether pins next to SSO bus are LVTTL/LVCMOS inputs, LVTTL/LVCMOS outputs, or GTL/SSTL/HSTL/LVDS/LVPECL inputs and outputs. Board traces in the vicinity of the SSO bus have to be adequately shielded from mutual coupling and inductive noise that can be generated by the SSO bus. Also, noise generated by the SSO bus needs to be reduced inside the package.

PCBs perform an important function in feeding stable supply voltages to the IC and, at the same time, maintaining signal integrity between devices.

Key issues that need to considered are as follows:

- Power and ground plane design and decoupling network design
- Transmission line reflections and terminations

***Table 2-81* • Fusion Pro I/O Default Attributes**

I/O Standards	SLEW (output only)	OUT_DRIVE (output only)	SKEW (tribuf and bibuf only)	RES_PULL	OUT_LOAD (output only)	COMBINE_REGISTER	IN_DELAY (input only)	IN_DELAY_VAL (input only)	SCHMITT_TRIGGER (input only)
LVTTL/LVCMOS 3.3 V	Refer to the following tables for more information: Table 2-78 on page 2-152 Table 2-79 on page 2-152 Table 2-80 on page 2-152	Refer to the following tables for more information: Table 2-78 on page 2-152 Table 2-79 on page 2-152 Table 2-80 on page 2-152	Off	None	35 pF	–	Off	0	Off
LVCMOS 2.5 V			Off	None	35 pF	–	Off	0	Off
LVCMOS 2.5/5.0 V			Off	None	35 pF	–	Off	0	Off
LVCMOS 1.8 V			Off	None	35 pF	–	Off	0	Off
LVCMOS 1.5 V			Off	None	35 pF	–	Off	0	Off
PCI (3.3 V)			Off	None	10 pF	–	Off	0	Off
PCI-X (3.3 V)			Off	None	10 pF	–	Off	0	Off
GTL+ (3.3 V)			Off	None	10 pF	–	Off	0	Off
GTL+ (2.5 V)			Off	None	10 pF	–	Off	0	Off
GTL (3.3 V)			Off	None	10 pF	–	Off	0	Off
GTL (2.5 V)			Off	None	10 pF	–	Off	0	Off
HSTL Class I			Off	None	20 pF	–	Off	0	Off
HSTL Class II			Off	None	20 pF	–	Off	0	Off
SSTL2 Class I and II			Off	None	30 pF	–	Off	0	Off
SSTL3 Class I and II			Off	None	30 pF	–	Off	0	Off
LVDS, BLVDS, M-LVDS			Off	None	0 pF	–	Off	0	Off
LVPECL			Off	None	0 pF	–	Off	0	Off

Table 2-96 • I/O Output Buffer Maximum Resistances [1] (continued)

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (ohms) [2]	$R_{PULL\text{-}UP}$ (ohms) [3]
HSTL (I)	8 mA	50	50
HSTL (II)	15 mA	25	25
SSTL2 (I)	17 mA	27	31
SSTL2 (II)	21 mA	13	15
SSTL3 (I)	16 mA	44	69
SSTL3 (II)	24 mA	18	32
Applicable to Advanced I/O Banks			
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	17	50
	24 mA	11	33
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
	16 mA	20	40
	24 mA	11	22
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
	12 mA	20	22
	16 mA	20	22
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
	6 mA	67	75
	8 mA	33	37
	12 mA	33	37
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. *These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCC, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website: http://www.microsemi.com/soc/techdocs/models/ibis.html.*
2. $R_{(PULL\text{-}DOWN\text{-}MAX)} = VOLspec / I_{OLspec}$
3. $R_{(PULL\text{-}UP\text{-}MAX)} = (VCCImax – VOHspec) / IOHspec$

Timing Characteristics

***Table 2-128* • 1.5 V LVCMOS Low Slew**
Commercial Temperature Range Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 1.4 V
Applicable to Pro I/Os

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	14.11	0.04	1.70	2.14	0.43	14.37	13.14	3.40	2.68	16.61	15.37	ns
	–1	0.56	12.00	0.04	1.44	1.82	0.36	12.22	11.17	2.90	2.28	14.13	13.08	ns
	–2	0.49	10.54	0.03	1.27	1.60	0.32	10.73	9.81	2.54	2.00	12.40	11.48	ns
4 mA	Std.	0.66	11.23	0.04	1.70	2.14	0.43	11.44	9.87	3.77	3.36	13.68	12.10	ns
	–1	0.56	9.55	0.04	1.44	1.82	0.36	9.73	8.39	3.21	2.86	11.63	10.29	ns
	–2	0.49	8.39	0.03	1.27	1.60	0.32	8.54	7.37	2.81	2.51	10.21	9.04	ns
8 mA	Std.	0.66	10.45	0.04	1.70	2.14	0.43	10.65	9.24	3.84	3.55	12.88	11.48	ns
	–1	0.56	8.89	0.04	1.44	1.82	0.36	9.06	7.86	3.27	3.02	10.96	9.76	ns
	–2	0.49	7.81	0.03	1.27	1.60	0.32	7.95	6.90	2.87	2.65	9.62	8.57	ns
12 mA	Std.	0.66	10.02	0.04	1.70	2.14	0.43	10.20	9.23	3.97	4.22	12.44	11.47	ns
	–1	0.56	8.52	0.04	1.44	1.82	0.36	8.68	7.85	3.38	3.59	10.58	9.75	ns
	–2	0.49	7.48	0.03	1.27	1.60	0.32	7.62	6.89	2.97	3.15	9.29	8.56	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to Table 3-7 on page 3-9.

***Table 2-129* • 1.5 V LVCMOS High Slew**
Commercial Temperature Range Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 1.4 V
Applicable to Pro I/Os

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	8.53	0.04	1.70	2.14	0.43	7.26	8.53	3.39	2.79	9.50	10.77	ns
	–1	0.56	7.26	0.04	1.44	1.82	0.36	6.18	7.26	2.89	2.37	8.08	9.16	ns
	–2	0.49	6.37	0.03	1.27	1.60	0.32	5.42	6.37	2.53	2.08	7.09	8.04	ns
4 mA	Std.	0.66	5.41	0.04	1.70	2.14	0.43	5.22	5.41	3.75	3.48	7.45	7.65	ns
	–1	0.56	4.60	0.04	1.44	1.82	0.36	4.44	4.60	3.19	2.96	6.34	6.50	ns
	–2	0.49	4.04	0.03	1.27	1.60	0.32	3.89	4.04	2.80	2.60	5.56	5.71	ns
8 mA	Std.	0.66	4.80	0.04	1.70	2.14	0.43	4.89	4.75	3.83	3.67	7.13	6.98	ns
	–1	0.56	4.09	0.04	1.44	1.82	0.36	4.16	4.04	3.26	3.12	6.06	5.94	ns
	–2	0.49	3.59	0.03	1.27	1.60	0.32	3.65	3.54	2.86	2.74	5.32	5.21	ns
12 mA	Std.	0.66	4.42	0.04	1.70	2.14	0.43	4.50	3.62	3.96	4.37	6.74	5.86	ns
	–1	0.56	3.76	0.04	1.44	1.82	0.36	3.83	3.08	3.37	3.72	5.73	4.98	ns
	–2	0.49	3.30	0.03	1.27	1.60	0.32	3.36	2.70	2.96	3.27	5.03	4.37	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to Table 3-7 on page 3-9.

SSTL2 Class I

Stub-Speed Terminated Logic for 2.5 V memory bus standard (JESD8-9). Fusion devices support Class I. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-156 • Minimum and Maximum DC Input and Output Levels

SSTL2 Class I	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
15 mA	–0.3	VREF – 0.2	VREF + 0.2	3.6	0.54	VCCI – 0.62	15	15	87	83	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*

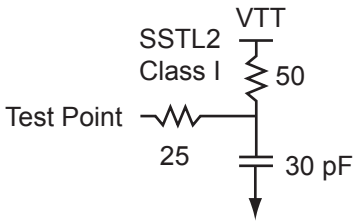


Figure 2-130 • AC Loading

Table 2-157 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C_{LOAD} (pF)
VREF – 0.2	VREF + 0.2	1.25	1.25	1.25	30

*Note: *Measuring point = Vtrip. See Table 2-90 on page 2-166 for a complete table of trip points.*

Timing Characteristics

Table 2-158 • SSTL 2 Class I
Commercial Temperature Range Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V, VREF = 1.25 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.66	2.13	0.04	1.33	0.43	2.17	1.85			4.40	4.08	ns
–1	0.56	1.81	0.04	1.14	0.36	1.84	1.57			3.74	3.47	ns
–2	0.49	1.59	0.03	1.00	0.32	1.62	1.38			3.29	3.05	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to Table 3-7 on page 3-9.

DDR Module Specifications

Input DDR Module

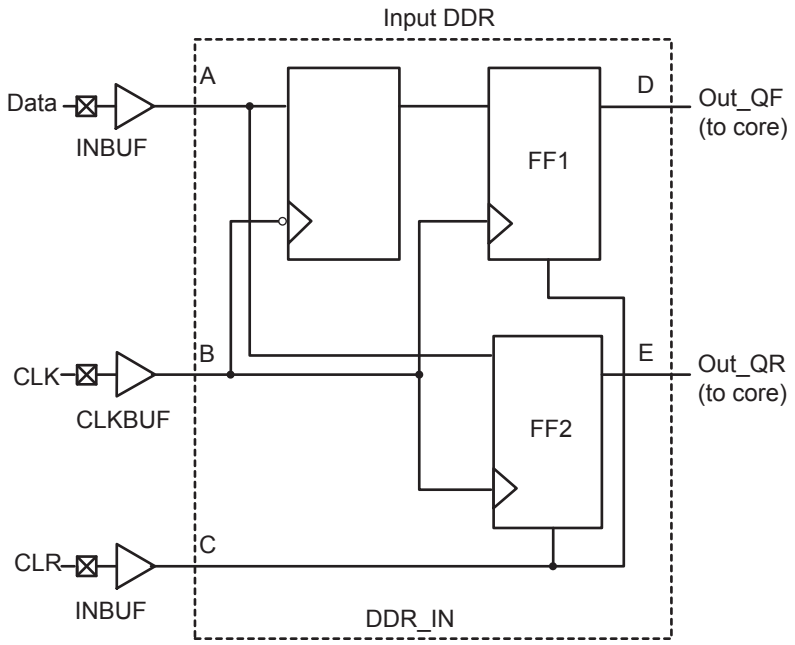


Figure 2-142 • **Input DDR Timing Model**

Table 2-179 • **Parameter Definitions**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
$t_{DDRICLKQ1}$	Clock-to-Out Out_QR	B, D
$t_{DDRICLKQ2}$	Clock-to-Out Out_QF	B, E
$t_{DDRISUD}$	Data Setup Time of DDR Input	A, B
t_{DDRIHD}	Data Hold Time of DDR Input	A, B
$t_{DDRICLR2Q1}$	Clear-to-Out Out_QR	C, D
$t_{DDRICLR2Q2}$	Clear-to-Out Out_QF	C, E
$t_{DDRIREMCLR}$	Clear Removal	C, B
$t_{DDRIRECCLR}$	Clear Recovery	C, B

Table 3-9 • AFS600 Quiescent Supply Current Characteristics (continued)

Parameter	Description	Conditions	Temp.	Min	Typ	Max	Unit
IPP	Programming supply current	Non-programming mode, VPUMP = 3.63 V	T_J = 25°C		36	80	µA
			T_J = 85°C		36	80	µA
			T_J = 100°C		36	80	µA
		Standby mode[5] or Sleep mode[6], VPUMP = 0 V			0	0	µA
ICCNVM	Embedded NVM current	Reset asserted, VCCNVM = 1.575 V	T_J = 25°C		22	80	µA
			T_J = 85°C		24	80	µA
			T_J = 100°C		25	80	µA
ICCPLL	1.5 V PLL quiescent current	Operational standby, VCCPLL = 1.575 V	T_J = 25°C		130	200	µA
			T_J = 85°C		130	200	µA
			T_J = 100°C		130	200	µA

Notes:

1. *ICC is the 1.5 V power supplies, ICC and ICC15A.*
2. *ICC33A includes ICC33A, ICC33PMP, and ICCOSC.*
3. *ICCI includes all ICCI0, ICCI1, ICCI2, and ICCI4.*
4. *Operational standby is when the Fusion device is powered up, all blocks are used, no I/O is toggling, Voltage Regulator is loaded with 200 mA, VCC33PMP is ON, XTAL is ON, and ADC is ON.*
5. *XTAL is configured as high gain, VCC = VJTAG = VPUMP = 0 V.*
6. *Sleep Mode, VCC = VJTAG = VPUMP = 0 V.*

***Table 3-10* • AFS250 Quiescent Supply Current Characteristics**

Parameter	Description	Conditions	Temp.	Min	Typ	Max	Unit
ICC[1]	1.5 V quiescent current	Operational standby[4], VCC = 1.575 V	T_J = 25°C		4.8	10	mA
			T_J = 85°C		8.2	30	mA
			T_J = 100°C		15	50	mA
		Standby mode[5] or Sleep mode[6], VCC = 0 V			0	0	µA
ICC33[2]	3.3 V analog supplies current	Operational standby[4], VCC33 = 3.63 V	T_J = 25°C		9.8	13	mA
			T_J = 85°C		9.8	14	mA
			T_J = 100°C		10.8	15	mA
		Operational standby, only Analog Quad and –3.3 V output ON, VCC33 = 3.63 V	T_J = 25°C		0.29	2	mA
			T_J = 85°C		0.31	2	mA
			T_J = 100°C		0.45	2	mA
		Standby mode[5], VCC33 = 3.63V	T_J = 25°C		2.9	3.0	mA
			T_J = 85°C		2.9	3.1	mA
			T_J = 100°C		3.5	6	mA
		Sleep mode[6], VCC33 = 3.63 V	T_J = 25°C		19	18	µA
			T_J = 85°C		19	20	µA
			T_J = 100°C		24	25	µA
ICCI[3]	I/O quiescent current	Operational standby[6], VCCIx = 3.63 V	T_J = 25°C		266	437	µA
			T_J = 85°C		266	437	µA
			T_J = 100°C		266	437	µA
IJTAG	JTAG I/O quiescent current	Operational standby[4], VJTAG = 3.63 V	T_J = 25°C		80	100	µA
			T_J = 85°C		80	100	µA
			T_J = 100°C		80	100	µA
		Standby mode[5] or Sleep mode[6], VJTAG = 0 V			0	0	µA

Notes:

1. *ICC is the 1.5 V power supplies, ICC, ICCPLL, ICC15A, ICCNVM.*
2. *ICC33A includes ICC33A, ICC33PMP, and ICCOSC.*
3. *ICCI includes all ICCI0, ICCI1, and ICCI2.*
4. *Operational standby is when the Fusion device is powered up, all blocks are used, no I/O is toggling, Voltage Regulator is loaded with 200 mA, VCC33PMP is ON, XTAL is ON, and ADC is ON.*
5. *XTAL is configured as high gain, VCC = VJTAG = VPUMP = 0 V.*
6. *Sleep Mode, VCC = VJTA G = VPUMP = 0 V.*

Table 3-13 • **Summary of I/O Output Buffer Power (per pin)—Default I/O Software Settings[1]**

	C_{LOAD} (pF)	VCCI (V)	Static Power PDC8 (mW)[2]	Dynamic Power PAC10 (µW/MHz)[3]
Applicable to Pro I/O Banks				
Single-Ended				
3.3 V LVTTL/LVCMOS	35	3.3	–	474.70
2.5 V LVCMOS	35	2.5	–	270.73
1.8 V LVCMOS	35	1.8	–	151.78
1.5 V LVCMOS (JESD8-11)	35	1.5	–	104.55
3.3 V PCI	10	3.3	–	204.61
3.3 V PCI-X	10	3.3	–	204.61
Voltage-Referenced				
3.3 V GTL	10	3.3	–	24.08
2.5 V GTL	10	2.5	–	13.52
3.3 V GTL+	10	3.3	–	24.10
2.5 V GTL+	10	2.5	–	13.54
HSTL (I)	20	1.5	7.08	26.22
HSTL (II)	20	1.5	13.88	27.22
SSTL2 (I)	30	2.5	16.69	105.56
SSTL2 (II)	30	2.5	25.91	116.60
SSTL3 (I)	30	3.3	26.02	114.87
SSTL3 (II)	30	3.3	42.21	131.76
Differential				
LVDS	–	2.5	7.70	89.62
LVPECL	–	3.3	19.42	168.02
Applicable to Advanced I/O Banks				
Single-Ended				
3.3 V LVTTL / 3.3 V LVCMOS	35	3.3	–	468.67
2.5 V LVCMOS	35	2.5	–	267.48
1.8 V LVCMOS	35	1.8	–	149.46
1.5 V LVCMOS (JESD8-11)	35	1.5	–	103.12
3.3 V PCI	10	3.3	–	201.02
3.3 V PCI-X	10	3.3	–	201.02

Notes:

1. *Dynamic power consumption is given for standard load and software-default drive strength and output slew.*
2. *PDC8 is the static power (where applicable) measured on VCCI.*
3. *PAC10 is the total dynamic power measured on VCC and VCCI.*

Methodology

Total Power Consumption—P_{TOTAL}

Operating Mode, Standby Mode, and Sleep Mode

$P_{TOTAL} = P_{STAT} + P_{DYN}$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption—P_{STAT}

Operating Mode

$P_{STAT} = PDC1 + (N_{NVM\text{-}BLOCKS} * PDC4) + PDC5+ (N_{QUADS} * PDC6) + (N_{INPUTS} * PDC7) + (N_{OUTPUTS} * PDC8) + (N_{PLLS} * PDC9)$

$N_{NVM\text{-}BLOCKS}$ is the number of NVM blocks available in the device.

N_{QUADS} is the number of Analog Quads used in the design.

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

N_{PLLS} is the number of PLLs available in the device.

Standby Mode

$P_{STAT} = PDC2$

Sleep Mode

$P_{STAT} = PDC3$

Total Dynamic Power Consumption—P_{DYN}

Operating Mode

$P_{DYN} = P_{CLOCK} + P_{S\text{-}CELL} + P_{C\text{-}CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL} + P_{NVM} + P_{XTL\text{-}OSC} + P_{RC\text{-}OSC} + P_{AB}$

Standby Mode

$P_{DYN} = P_{XTL\text{-}OSC}$

Sleep Mode

$P_{DYN} = 0$ W

Global Clock Dynamic Contribution—P_{CLOCK}

Operating Mode

$P_{CLOCK} = (PAC1 + N_{SPINE} * PAC2 + N_{ROW} * PAC3 + N_{S\text{-}CELL} * PAC4) * F_{CLK}$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *Fusion and Extended Temperature Fusion FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *Fusion and Extended Temperature Fusion FPGA Fabric User's Guide*.

F_{CLK} is the global clock signal frequency.

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design.

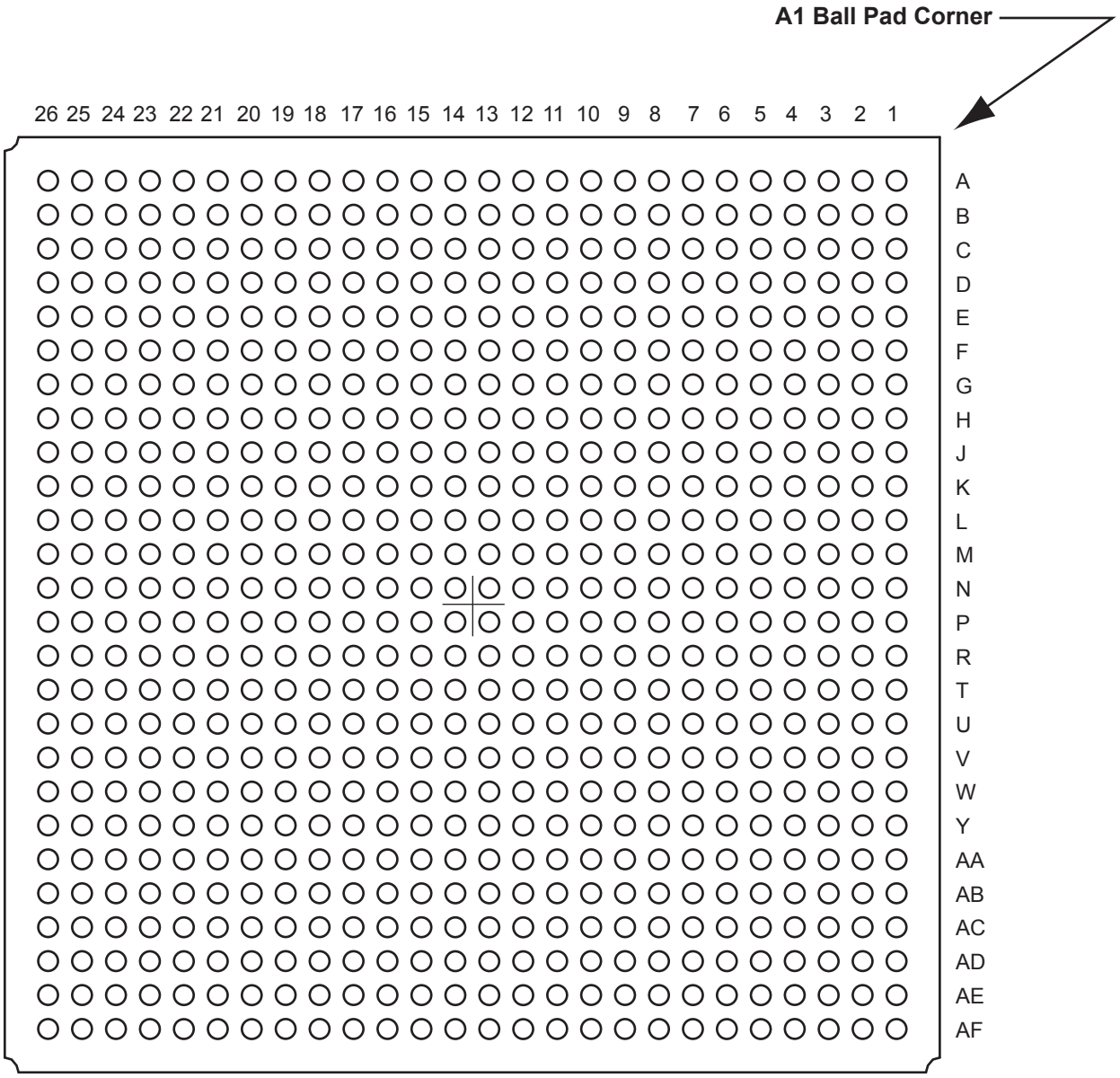
Standby Mode and Sleep Mode

$P_{CLOCK} = 0$ W

Sequential Cells Dynamic Contribution—$P_{S\text{-}CELL}$

Operating Mode

FG676



Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/default.aspx.

FG676	
Pin Number	**AFS1500 Function**
L17	VCCIB2
L18	GCB2/IO60PDB2V0
L19	IO58NDB2V0
L20	IO57NDB2V0
L21	IO59NDB2V0
L22	GCC2/IO61PDB2V0
L23	IO55PPB2V0
L24	IO56PDB2V0
L25	IO55NPB2V0
L26	GND
M1	NC
M2	VCCIB4
M3	GFC2/IO108PDB4V0
M4	GND
M5	IO109NDB4V0
M6	IO110NDB4V0
M7	GND
M8	IO104NDB4V0
M9	IO111NDB4V0
M10	GND
M11	V**CC**
M12	GND
M13	VCC
M14	GND
M15	VCC
M16	GND
M17	GND
M18	IO60NDB2V0
M19	IO58PDB2V0
M20	GND
M21	IO68NPB2V0
M22	IO61NDB2V0
M23	GND
M24	IO56NDB2V0
M25	VCCIB2
M26	IO65PDB2V0

FG676	
Pin Number	**AFS1500 Function**
N1	NC
N2	NC
N3	IO108NDB4V0
N4	VCCOSC
N5	VCCIB4
N6	XTAL2
N7	GFC1/IO107PDB4V0
N8	VCCIB4
N9	GFB1/IO106PDB4V0
N10	VCCIB4
N11	GND
N12	VCC
N13	GND
N14	VCC
N15	GND
N16	VCC
N17	VCCIB2
N18	IO70PDB2V0
N19	VCCIB2
N20	IO69PDB2V0
N21	GCA1/IO64PDB2V0
N22	VCCIB2
N23	GCC0/IO62NDB2V0
N24	GCC1/IO62PDB2V0
N25	IO66PDB2V0
N26	IO65NDB2V0
P1	NC
P2	NC
P3	IO103PDB4V0
P4	XTAL1
P5	VCCIB4
P6	GNDOSC
P7	GFC0/IO107NDB4V0
P8	VCCIB4
P9	GFB0/IO106NDB4V0
P10	VCCIB4

FG676	
Pin Number	**AFS1500 Function**
P11	VCC
P12	GND
P13	VCC
P14	GND
P15	VCC
P16	GND
P17	VCCIB2
P18	IO70NDB2V0
P19	VCCIB2
P20	IO69NDB2V0
P21	GCA0/IO64NDB2V0
P22	VCCIB2
P23	GCB0/IO63NDB2V0
P24	GCB1/IO63PDB2V0
P25	IO66NDB2V0
P26	IO67PDB2V0
R1	NC
R2	VCCIB4
R3	IO103NDB4V0
R4	GND
R5	IO101PDB4V0
R6	IO100NPB4V0
R7	GND
R8	IO99PDB4V0
R9	IO97PDB4V0
R10	GND
R11	GND
R12	VCC
R13	GND
R14	VCC
R15	GND
R16	VCC
R17	GND
R18	GDB2/IO83PDB2V0
R19	IO78PDB2V0
R20	GND